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10-06-2012 19

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((((lithograph$6 optical$2) near2 limit) sub-lithograph$6
) near9 (sidewall adj oxide spacer) and (((FOX field adj oxide ST1 (isolat$3 (element adj (insulat$4
separat$4)) adj2 (oxide region film structure) ) locos)
) ) near ((trench$4 groove$2)
)) ) (((trench$4 groove$2)
) near4 depth) with (((memory cell array core) ) adj ((area region section portion)
)) near6 ((peripher$2 logic ) adj ((area region section portion)
))) )

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Jan. 2005

	U	Inventor	Document	Issue P	Title	Current	Current X	Retrieval	S	C	P	Image Do P	
1	<input type="checkbox"/>	Tseng, Hor	US 641383	2002	8	Method of making isolation trench	438/42	257/510		<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 64138
2	<input checked="" type="checkbox"/>	Nishioka, N	US 599473	1999	3	Nonvolatile semiconductor memory de	257/31	257/315		<input type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 59947
3	<input checked="" type="checkbox"/>	Dokumaci, US	200401	2004	1	DAMASCENE METHOD FOR IMPROV	257/37	257/382		<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040
4	<input checked="" type="checkbox"/>	Hsu, Louis	US 200401	2004	2	Vertical MOSFET SRAM cell	257/36	257/379		<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040
5	<input checked="" type="checkbox"/>	Wicker, Gu	US 200401	2004	1	Phase change memory and method th	257/29	257/209		<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040
6	<input checked="" type="checkbox"/>	Wicker, Gu	US 200401	2004	1	Lateral phase change memory and me	257/24			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040
7	<input checked="" type="checkbox"/>	Dennison, US	200401	2004	2	PHASE CHANGE MEMORY AND MET	257/2	257/4	25	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040
8	<input checked="" type="checkbox"/>	Parat, Krish	US 200400	2004	2	Dual trench isolation using single critic	438/42	257/E21.5		<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040
9	<input checked="" type="checkbox"/>	Kim, Jum S	US 200400	2004	1	Method of manufacturing flash memor	438/25	257/E21.5		<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040
10	<input checked="" type="checkbox"/>	Noro, Fumi	US 200302	2003	3	Semiconductor memory and method fo	257/29	257/E21.6		<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030